b) Amendments to the Claims:

Please amend claims 1, 11, 12 and 13 as follows. In accordance with the Revised Amendment Format, the status of all claims are presented below.

1. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode separate from said substrate is arranged in plasma in the vacuum vessel, and a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, wherein a voltage lower than the potential of plasma is applied to the auxiliary electrode to avoid discharge and to form ~~a~~ the deposited film while controlling generation of hydrogen radicals.

2. (Cancelled)

3. (Original) The deposited-film formation method according to claim 2, wherein the maximum amplitude of the voltage is 20 V to 80 V.

4. (Original) The deposited-film formation method according to claim 2, wherein the maximum amplitude of the voltage is 20 V to 60 V.

5. (Original) The deposited-film formation method according to claim 1, wherein when the periodically changing voltage is applied to the auxiliary electrode, a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage.

6. (Previously Presented) The deposited-film formation method according to claim 1, wherein a plurality of said auxiliary electrodes is arranged at least in a flow direction of the material gas.

7. - 8. (Cancelled)

9. (Original) The deposited-film formation method according to claim 1, wherein the auxiliary electrode is formed from an edgeless and small electrode having a small area facing a substrate in the vacuum vessel.

10. (Previously Presented ) The deposited-film formation method according to claim 1, wherein the auxiliary electrode is formed from a round bar which has a small diameter and which is made of a high strength material of a high melting point metal.

11. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode separate from said substrate is arranged in plasma in the vacuum vessel, a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode so that a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage to accelerate electrons at minimum voltage with minimal effect on the plasma, thereby forming a the deposited film and controlling generation of hydrogen radicals.

12. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode separate from said substrate is arranged in plasma in the vacuum vessel, a high-frequency power of 1 MHz to 200 MHz is applied to the discharge electrode, and a high-frequency power of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, wherein a voltage lower than the potential of plasma is applied to the auxiliary electrode to avoid discharge, thereby forming ~~a~~ the deposited film and controlling generation of hydrogen radicals.

13. (Currently Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode separate from said substrate is arranged in plasma in the vacuum vessel, a periodic electric field having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, and only electrons are energized without energizing ions to discompose a hydrogen gas and generate hydrogen radicals to provide a voltage lower than the potential of plasma to avoid discharge, thereby forming a the deposited film and controlling the generation of the hydrogen radicals.

14. - 26. (Cancelled)

27. (Previously Presented) The deposited-film formation method according to claim 1, wherein said auxiliary electrode is arranged in the plasma and between said discharge electrode and said substrate.